

ABSTRACT

A capacitance type MEMS device capable of obtaining favorable switching characteristics relative to high frequency signals, a manufacturing method thereof, and a high performance high frequency device mounting the capacitance type MEMS device are provided. A typical example of the device of the present invention has a conductor layer formed on a dielectric film. The dielectric film is formed on a lower electrode opposed to an upper electrode made of a metal film. The upper electrode vertically moves. The area of a region where the conductor layer formed on the dielectric layer is present in a region where the upper electrode and the lower electrode are opposed is equal to or smaller than the area of the region where the conductor layer formed on the dielectric layer is not present in the opposed region.